

Number	Hits	Search Text	DB	Time stamp
13	2	("20030094667").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:11
14	1	light near receiving near element and (("20030094667").PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:24
15	0	JP-64090570-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:20
16	0	JP-6490570-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:20
17	0	JP-06490570-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:20
18	0	JP-60490570-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:20
19	35199	light near receiving near element	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:28
22	25431	371/\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:26
23	43	(light near receiving near element) and 371/\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:27
24	2393	edge near (emitting incidence)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:28
25	5	edge near (emitting incidence) with light near receiving near element	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:32
26	8	edge near (emitting incidence) with light near (sens\$3 receiv\$4 detect\$3) near element	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:33

27	3	(edge near (emitting incidence) with light near (sens\$3 receiv\$4 detect\$3) near element) not (edge near (emitting incidence) with light near receiving near element)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/23 17:33
-	4	light adj receiv\$3 adj element same position adj marker	USPAT	2001/09/17 16:43
-	4	light adj receiv\$3 adj element same position adj marker	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 15:52
-	255	(257/434,444).CCLS.	USPAT	2002/05/10 14:33
-	637	(257/434,444).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 16:46
-	93	((("257/434,444").CCLS.) and align\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 17:01
-	0	((("257/434,444").CCLS.) and align\$6) and ("InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 11:55
-	1	((("257/434,444").CCLS.) and ("InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 17:04
-	1	((("257/434,444").CCLS.) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 08:57
-	9494	(257/431-466).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 08:45
-	16	((("257/431-466").CCLS.) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 17:16
-	1791	light with align\$6 and (257/\$ 438/\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 17:18
-	4457	optical adj guide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 17:26
-	5	(light with align\$6 and (257/\$ 438/\$)) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 17:28

-	21	(optical adj guide) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 17:31
-	3934	mount\$3 same semiconductor same align\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 08:46
-	9498	(257/431-466).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 08:45
-	58	(mount\$3 same semiconductor same align\$6) and ((("257/431-466").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 08:58
-	1488	(mount\$3 with semiconductor with align\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:06
-	21	(mount\$3 with semiconductor with align\$6) and ((("257/431-466").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:19
-	0	((mount\$3 with semiconductor with align\$6)) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:08
-	3938	(mount\$3 same semiconductor same align\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 08:58
-	2	((mount\$3 same semiconductor same align\$6)) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:15
-	0	((mount\$3 same semiconductor same align\$6)) and (InalgaAs "InalgaAs" "In al ga As" i adj "InalgaAs" "i-InalgaAs" "i - In al ga As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:11
-	0	((mount\$3 with semiconductor with align\$6)) and (InalgaAs "InalgaAs" "In al ga As" i adj "InalgaAs" "i-InalgaAs" "i - In al ga As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:16
-	155688	(mount\$3 with align\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:20

-	2	((mount\$3 with align\$6)) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:48
-	0	Toshiyuki adj Mogi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:48
-	67796	Toshiyuki	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:49
-	168	Toshiyuki and Kazumi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:49
-	3	Toshiyuki and Kazumi and shinji	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 09:50
-	2	Toshiyuki and Kazumi and photodetector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:01
-	4	Toshiyuki and Kazumi and align\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:01
-	2095	(light with semiconductor with align\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:08
-	684	((light with semiconductor with align\$6)) and align\$6 near2 (position\$3 point\$3 mark\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:26
-	0	((light with semiconductor with align\$6)) and align\$6 near2 (position\$3 point\$3 mark\$3)) and (InGaAlAs "InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:16
-	0	((light with semiconductor with align\$6)) and align\$6 near2 (position\$3 point\$3 mark\$3)) and (InalgaAs "InalgaAs" "In al ga As" i adj "InalgaAs" "i-InalgaAs" "i - In al ga As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:16
-	5	light near (detect\$5 absorb\$5 reciev\$5) near (layer film) and (((light with semiconductor with align\$6)) and align\$6 near2 (position\$3 point\$3 mark\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:21

-	0	(photodetect\$5 photoabsorb\$5 photoreciev\$5) near (layer film) and (((light with semiconductor with align\$6)) and align\$6 near2 (position\$3 point\$3 mark\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:26
-	1	(photodetect\$5 photoabsorb\$5 photoreciev\$5) near2 (layer film) and (((light with semiconductor with align\$6)) and align\$6 near2 (position\$3 point\$3 mark\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:26
-	91	(438/\$ 257/\$) and (((light with semiconductor with align\$6)) and align\$6 near2 (position\$3 point\$3 mark\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 10:32
-	32	((257/\$ 438/\$) and align\$6) and ("InGaAlAs" "In Ga Al As" i adj "InGaAlAs" "i-InGaAlAs" "i - In Ga Al As")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/18 11:58
-	21	light\$3 near (detect\$4 reciev\$4) same alignment and (indium adj phosphide InP "IN P")	USPAT	2002/05/10 14:35
-	656	(257/434,444).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:33
-	2	light\$3 near (detect\$4 reciev\$4) same alignment and ((257/434,444).CCLS.)	USPAT	2002/05/10 14:36